

REMARKS

This is intended as a full and complete response to the Final Office Action dated November 7, 2007, having a shortened statutory period for response set to expire on February 7, 2008. Please reconsider the claims pending in the application for reasons discussed below.

Claims 15-18 and 21-28 remain pending in the application and are shown above. Claims 15-18 and 21-28 are rejected by the Examiner. Applicant has canceled claim 26 without prejudice. Reconsideration of the rejected claims is requested for reasons presented below.

Claims 15-18, 21 and 23-25, 27 and 28 are rejected under 35 U.S.C. § 103(a) as being unpatentable over *Chiang et al* (U.S. Pat. No. 5,817,572, hereinafter "Chiang") in view of *Matsuura* (U.S. Pat. No. 6,124,641, hereinafter "Matsuura"). Chiang and Matsuura have been discussed and cited before in the record of this application as grounds for rejection of these claims (*see* Office Action, December 22, 2005). Applicant respectfully traverses the rejection.

Matsuura discloses formation of a carbon-containing silicon oxide film from methylsilane and hydrogen peroxide by a chemical vapor deposition method. Matsuura also discloses formation of a silicon oxide film from silane and nitrous oxide by a plasma enhanced chemical vapor deposition method. Applicant responded to a previous rejection that there is no motivation or suggestion in the combination of Chiang and Matsuura to use a plasma enhanced deposition process to form the carbon-containing silicon oxide films described in Matsuura (*see* Response to Office Action, March 17, 2006). Thereafter, the ground of rejection over Chiang and Matsuura was not continued (*see, e.g.,* Office Action, May 12, 2006).

The Examiner has again rejected claims over the combination of Chiang and Matsuura on grounds that Matsuura describes plasma enhanced deposition of a carbon-containing silicon oxide film. The cited portion of the reference does not support this conclusion. Applicant maintains that Matsuura does not teach, show, or suggest depositing the claimed carbon-containing films by a plasma enhanced method. Applicant therefore maintains that Chiang and Matsuura, alone or in combination, do not

teach, show or suggest a method comprising depositing on a substrate a plurality of layers, wherein one or more of the layers is a low dielectric constant oxidized organosilane layer comprising carbon, wherein the low dielectric constant oxidized organosilane layer is deposited in a plasma enhanced process from a mixture comprising a methylsilane compound and an oxidizing gas, the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight, and a top layer of the plurality of layers is a photoresist, as recited in claim 15 and claims dependent thereon. Withdrawal of the rejection is respectfully requested.

Claim 22 is rejected under 35 U.S.C. § 103(a) as being unpatentable over *Chiang* ('572) in view of *Matsuura* ('641) as applied to claims 15-18, 21 and 23-25, 27, and 28 and further in view of *Chen* (U.S. Pat. No. 5,970,376, hereinafter "Chen"). *Chiang* and *Matsuura* are discussed above. *Chen* does not remedy the deficiency of *Chiang* and *Matsuura*. Withdrawal of the rejection is respectfully requested.

Claim 26 is rejected under 35 U.S.C. § 103(a) as being unpatentable over *Chiang* ('572) in view of *Matsuura* ('641) as applied to claims 15-18, 21 and 23-25, 27, and 28 and further in view of *Shu, et al.* (U.S. Pat. No. 6,348,421 B1, hereinafter "Shu"). Applicant has canceled claim 26 without prejudice. Withdrawal of the rejection is respectfully requested.

In conclusion, the references cited by the Examiner do not teach, show, or suggest the invention as claimed.

Having addressed all issues set out in the Final Office Action, Applicant respectfully submits that the claims are in condition for allowance and respectfully request that the claims be allowed.

Respectfully submitted,



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